



## Examples for the claim correspondence

The claims in the following cases are considered to “sufficiently correspond”.

### EX.1

| <i>OFF<sup>1</sup> claims</i> | <i>OSF<sup>2</sup> claims</i> | <i>Comment</i>  |
|-------------------------------|-------------------------------|---|
| 1                             | 1                             | <i>The OSF claim has the additional component on the OFF granted claim.</i> |

| OFF granted claim   | OSF claim   |
|---|---|
| <p>A system for presenting a container storing at least one article to a processing tool, comprising:</p> <p>(a) a load port, including:<br/>                     a frame having an opening;<br/>                     a support structure being adapted to receive a container, and<br/>                     a drive mechanism for moving said support structure substantially vertically between a first height and a second height; and</p> <p>(b) a conveyor for movably supporting the container substantially along a container transport plane;<br/>                     wherein a container traveling on said conveyor moves unobstructed over said support structure when said support structure is located in said second height,<br/>                     wherein the container traveling unobstructed does not contact said support structure while traveling over said support structure located at said second height,<br/>                     wherein said support structure, when located at said second height, is located below said transport plane.</p> <p><i>*This additional part is NOT included in the OFF granted claim but it is included in the description of the OFF application</i></p> | <p>A system for presenting a container storing at least one article to a processing tool, comprising:</p> <p>(a) a load port, including:<br/>                     a frame having an opening;<br/>                     a support structure being adapted to receive a container, and<br/>                     a drive mechanism for moving said support structure substantially vertically between a first height and a second height; and</p> <p>(b) a conveyor for movably supporting the container substantially along a container transport plane;<br/>                     wherein a container traveling on said conveyor moves unobstructed over said support structure when said support structure is located in said second height,<br/>                     wherein the container traveling unobstructed does not contact said support structure while traveling over said support structure located at said second height,<br/>                     wherein said support structure, when located at said second height, is located below said transport plane,<br/> <b><i>wherein said support structure, when located at said first height, is located above said transport plane*.</i></b></p> |

### EX.2

| <i>OFF claims</i> | <i>OSF claims</i> | <i>Comment</i>   |
|-------------------|-------------------|--|
| 1                 | 1                 | <i>Same</i>  |
| <i>none</i>       | 2                 | <i>The OSF claim2 is dependent on the OSF claim1, which has been granted at OFF.</i> |

| OFF granted claim   | OSF claim   |
|---|---|
| <p>1. A nitride-based semiconductor device comprising:<br/>                     a first semiconductor layer, consisting of either an n-type nitride-based semiconductor layer having a wurtzite structure or an n-type nitride-based semiconductor substrate having a wurtzite structure; and<br/>                     an n-side electrode formed on a back surface of said first semiconductor layer,<br/>                     wherein a dislocation density is not more than <math>1 \times 10^9 \text{ cm}^{-2}</math> in the vicinity of the interface between said first semiconductor layer and said n-side electrode, and<br/>                     contact resistance between said n-side electrode and said first semiconductor layer is not more than <math>0.05 \text{ } \Omega \text{ cm}^2</math></p> | <p>1. (Same)</p>  |
| <p>2. (None)</p>  | <p><b><i>2. The nitride-based semiconductor device according to claim 1, wherein said first semiconductor layer includes an n-type dopant.*</i></b></p> |

<sup>1</sup> Office of First Filing

<sup>2</sup> Office of Second Filing

*\*This additional part is NOT included in the OFF granted claim but it is included in the description of the OFF application*